

8550SS TRANSISTOR (PNP)

FEATURES

- General Purpose Switching and Amplification.

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

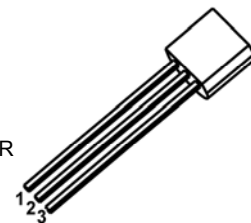
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

TO - 92

1.EMITTER

2.COLLECTOR

3.BASE



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	85		300	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800\text{mA}, I_B = -80\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -50\text{mA}, f = 30\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	B	C	D
RANGE	85-160	120-200	160-300

